

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Atty. Docket

ZHONGNING LIANG ET AL

NL 000195

Serial No.

Filed: CONCURRENTLY

SEMICONDUCTOR DEVICE

Honorable Commissioner of Patents and Trademarks
Washington, D.C. 20231

PRELIMINARY AMENDMENT

Sir:

Prior to calculation of the filing fee and examination, please amend the above-identified application as follows:

IN THE CLAIMS

Please amend the claims as follows:

3. (Amended) A semiconductor device as claimed in claim 1, wherein a stack of layered structures is present.

7. (Amended) A semiconductor device as claimed in claim 1, wherein the via lines are patterned in the form of a grid.

8. (Amended) A method of manufacturing a semiconductor device as claimed in claim 1, comprising the steps of:

- (a) forming a metal layer;
- (b) forming a dielectric layer;

- (c) patterning via lines or via grids in the dielectric layer;
- (d) filling the patterned via lines or via grids with a conductive material, such as a metal, and preferably tungsten or copper; and
- (e) applying a metal bond pad on top of the dielectric layer and the filled via lines or via grids.

11. (Amended) A method as claimed in claim 8, wherein the via lines or lines of metal are applied in the form of a grid.

REMARKS

The claims have been amended in order to reformat the claims to delete all multiple dependencies prior to calculation of the filing fee and place the instant application in standard U.S. format.

Entry of this amendment prior to calculating the filing fee is respectfully requested.

Respectfully submitted,

By 
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April 10, 2001

APPENDIX

3. (Amended) A semiconductor device as claimed in claim 1 ~~or 2~~, wherein a stack of layered structures is present.

7. (Amended) A semiconductor device as claimed in claim 1 ~~any one of the preceding claims~~, wherein the via lines are patterned in the form of a grid.

8. (Amended) A method of manufacturing a semiconductor device as claimed in claim 1 ~~any one of the preceding claims~~, comprising the steps of:

- (f) forming a metal layer;
- (g) forming a dielectric layer;
- (h) patterning via lines or via grids in the dielectric layer;
- (i) filling the patterned via lines or via grids with a conductive material, such as a metal, and preferably tungsten or copper; and
- (j) applying a metal bond pad on top of the dielectric layer and the filled via lines or via grids.

11. (Amended) A method as claimed in claim 8 ~~any one of claims 8 to 10~~, wherein the via lines or lines of metal are applied in the form of a grid.